

## P-channel -100 V, 0.136 $\Omega$ typ., -3 A STripFET™ F6 Power MOSFET in an SOT-223 package

Datasheet - preliminary data

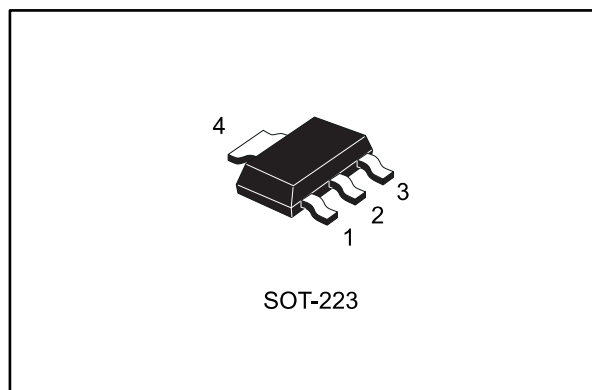
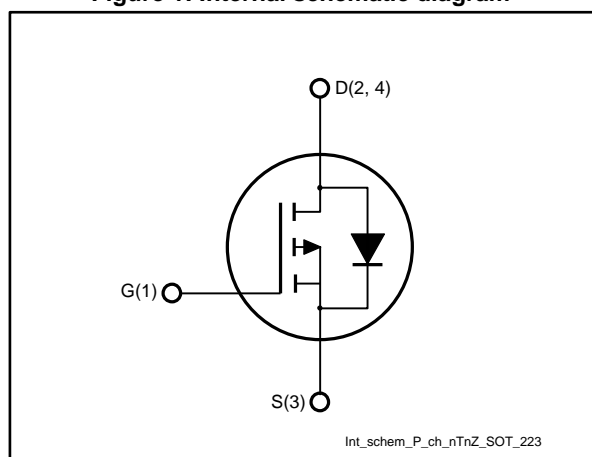


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STN3P10F6	-100 V	0.180 $\Omega$	-3 A

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

### Applications

- Switching applications

### Description

This device is a P-channel Power MOSFET developed using the STripFET™ F6 technology, with a new trench gate structure. The resulting Power MOSFET exhibits very low R<sub>DS(on)</sub> in all packages.

Table 1: Device summary

Order code	Marking	Package	Packing
STN3P10F6	3P10F6	SOT-223	Tape and reel

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	-100	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	-3	A
	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	-2	A
$I_{DM}$	Drain current (pulsed)	-12	A
$P_{TOT}^{(1)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	3.3	W
$T_j$	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		$^\circ\text{C}$

**Notes:**

<sup>(1)</sup>Pulse width is limited by safe operating area

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	46	$^\circ\text{C}/\text{W}$

**Notes:**

<sup>(1)</sup>When mounted on FR-4 board of 1 inch<sup>2</sup>, 2 Oz Cu,  $t < 10\text{ s}$

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4: On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = -1\text{ mA}$	-100			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = -100\text{ V}$			-1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = -100\text{ V}$ , $T_C = 125\text{ °C}^{(1)}$			-10	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = -250\text{ }\mu\text{A}$	-2		-4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = -10\text{ V}$ , $I_D = -1.5\text{ A}$		0.136	0.180	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = -25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	900	-	pF
$C_{oss}$	Output capacitance		-	60	-	pF
$C_{rss}$	Reverse transfer capacitance		-	33	-	pF
$Q_g$	Total gate charge	$V_{DD} = -50\text{ V}$ , $I_D = -3\text{ A}$ , $V_{GS} = -10\text{ V}$ (see <a href="#">Figure 14: "Gate charge test circuit"</a> )	-	16.5	-	nC
$Q_{gs}$	Gate-source charge		-	3.5	-	nC
$Q_{gd}$	Gate-drain charge		-	3.8	-	nC

**Table 6: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = -50\text{ V}$ , $I_D = -1.5\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = -10\text{ V}$ (see <a href="#">Figure 13: "Switching times test circuit for resistive load"</a> )	-	10.5	-	ns
$t_r$	Rise time		-	4.8	-	ns
$t_{d(off)}$	Turn-off delay time		-	24	-	ns
$t_f$	Fall time		-	4.5	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = -3 \text{ A}$ , $V_{GS} = 0 \text{ V}$	-		-1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = -3 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = -80 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	26.5		ns
$Q_{rr}$	Reverse recovery charge		-	36.5		nC
$I_{RRM}$	Reverse recovery current		-	-2.7		A

**Notes:**

<sup>(1)</sup>Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)



For the P-channel Power MOSFET, current and voltage polarities are reversed.

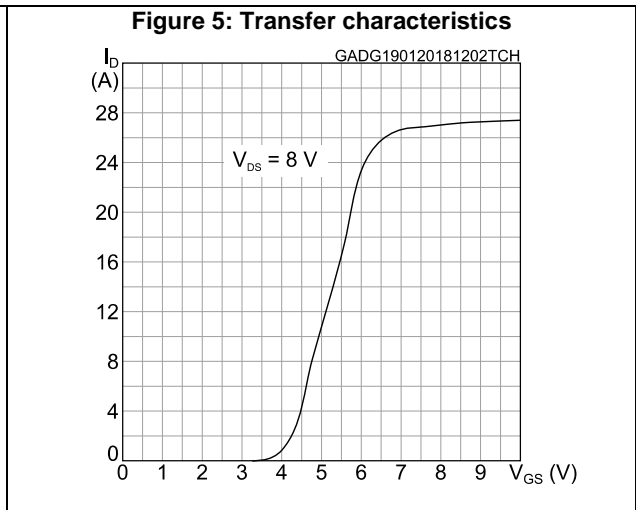
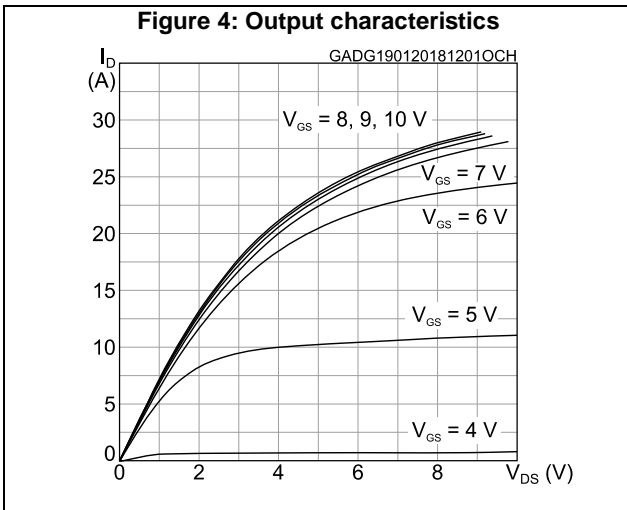
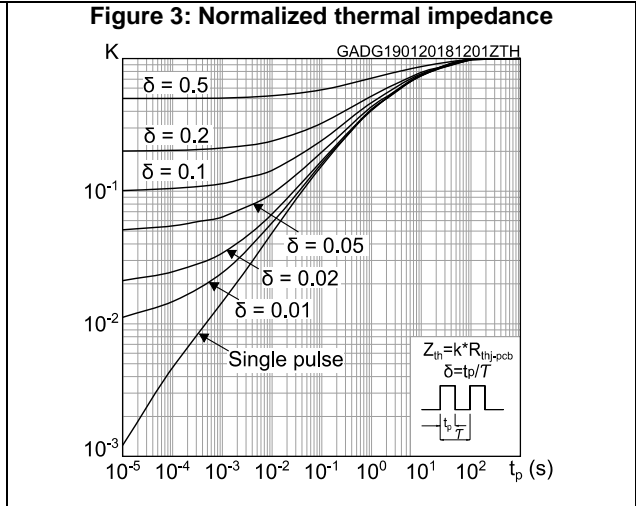
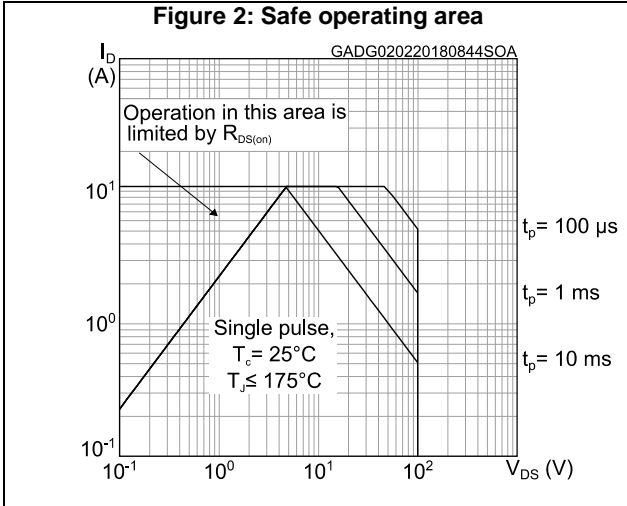


Figure 6: Gate charge vs gate-source voltage

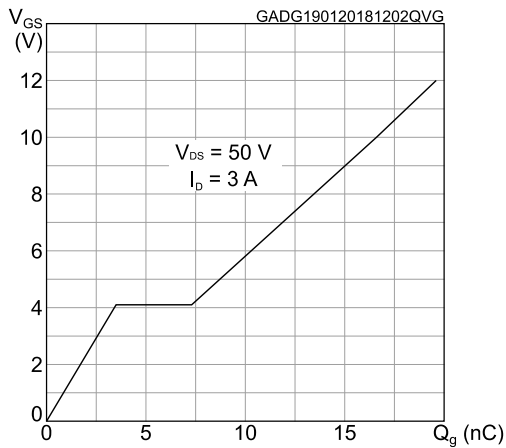


Figure 7: Capacitance variations

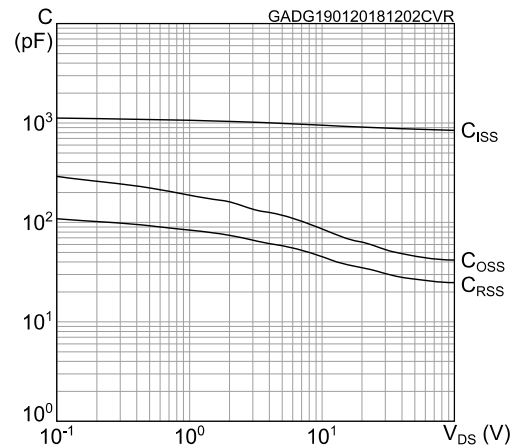


Figure 8: Static drain-source on-resistance

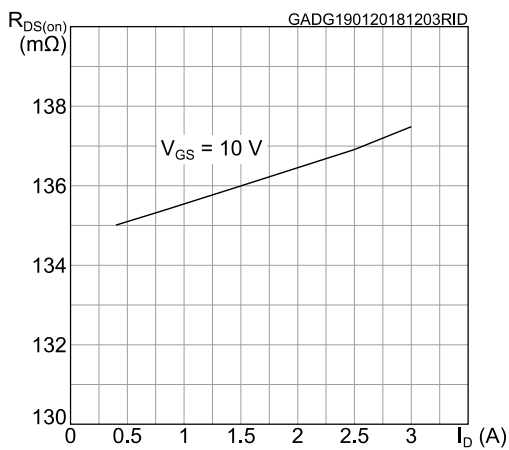


Figure 9: Normalized gate threshold voltage vs temperature

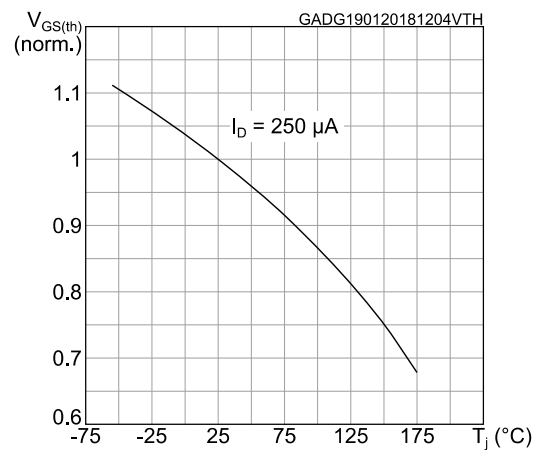


Figure 10: Normalized on-resistance vs temperature

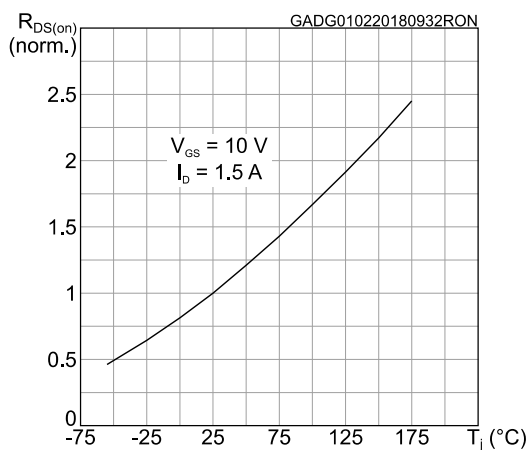


Figure 11: Normalized  $V_{(BR)DSS}$  vs temperature

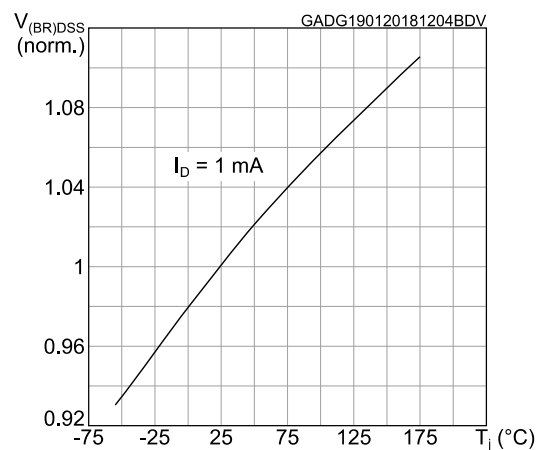
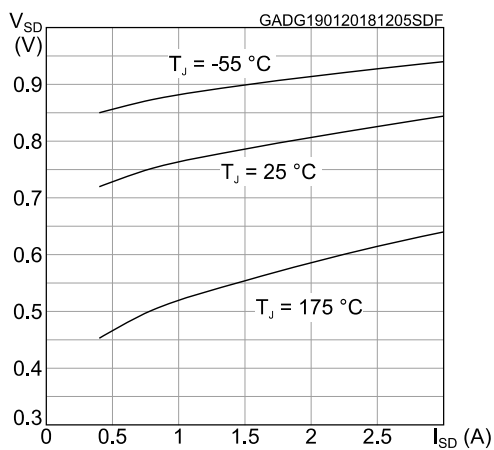


Figure 12: Source-drain diode forward characteristics





### 3 Test circuits

Figure 13: Switching times test circuit for resistive load

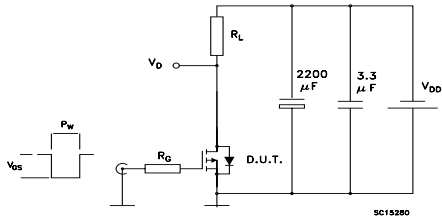


Figure 14: Gate charge test circuit

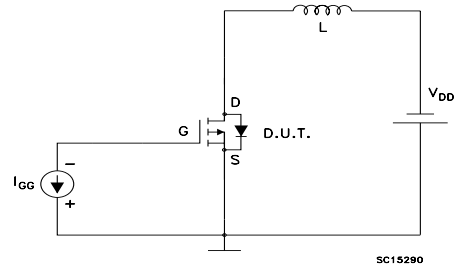
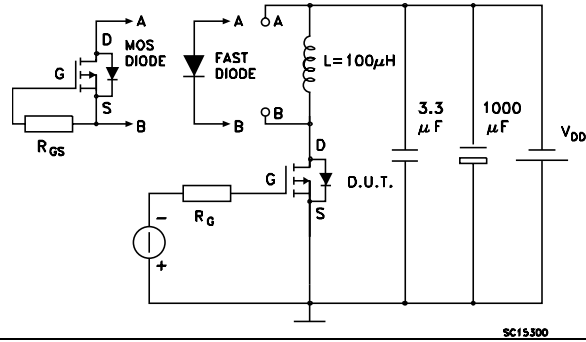


Figure 15: Test circuit for inductive load switching and diode recovery times

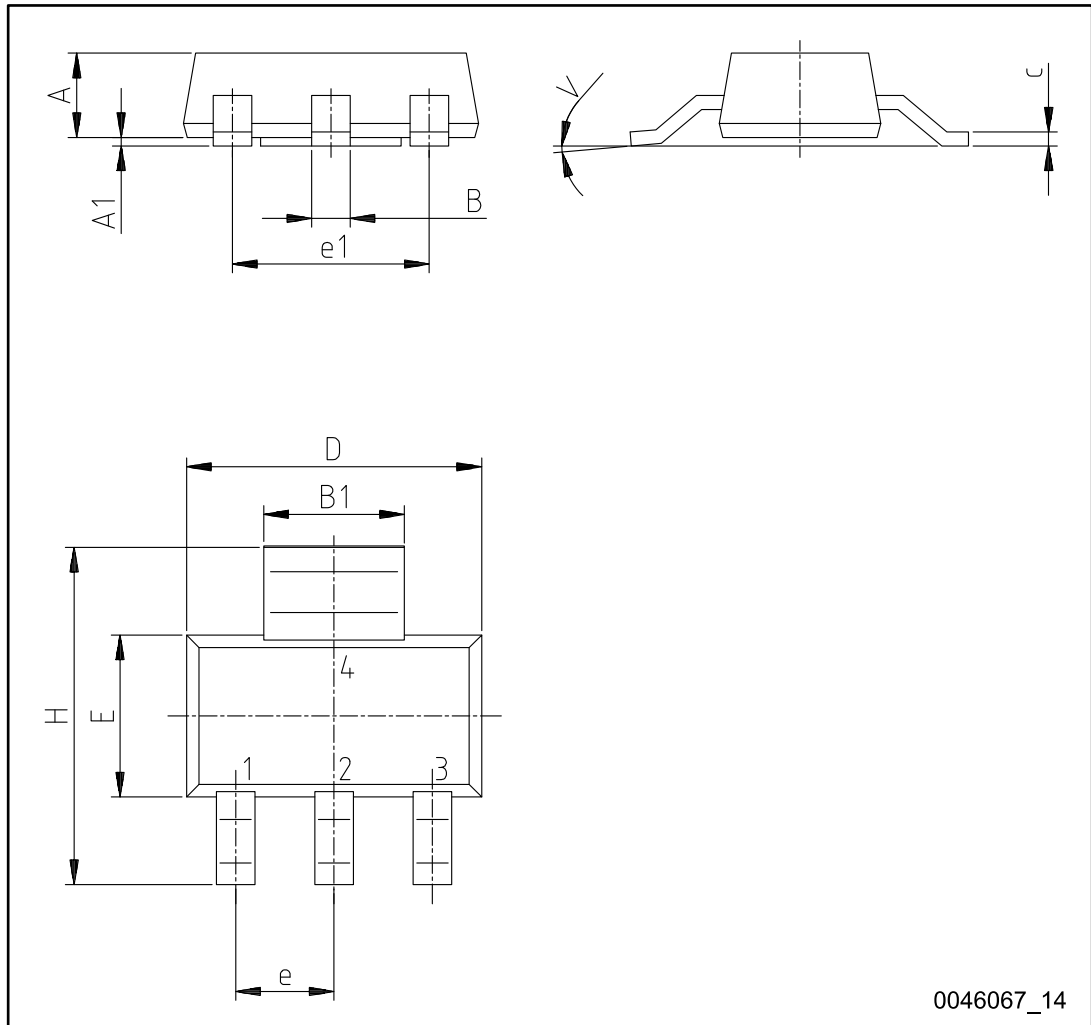


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 SOT-223 package information

Figure 16: SOT-223 package outline

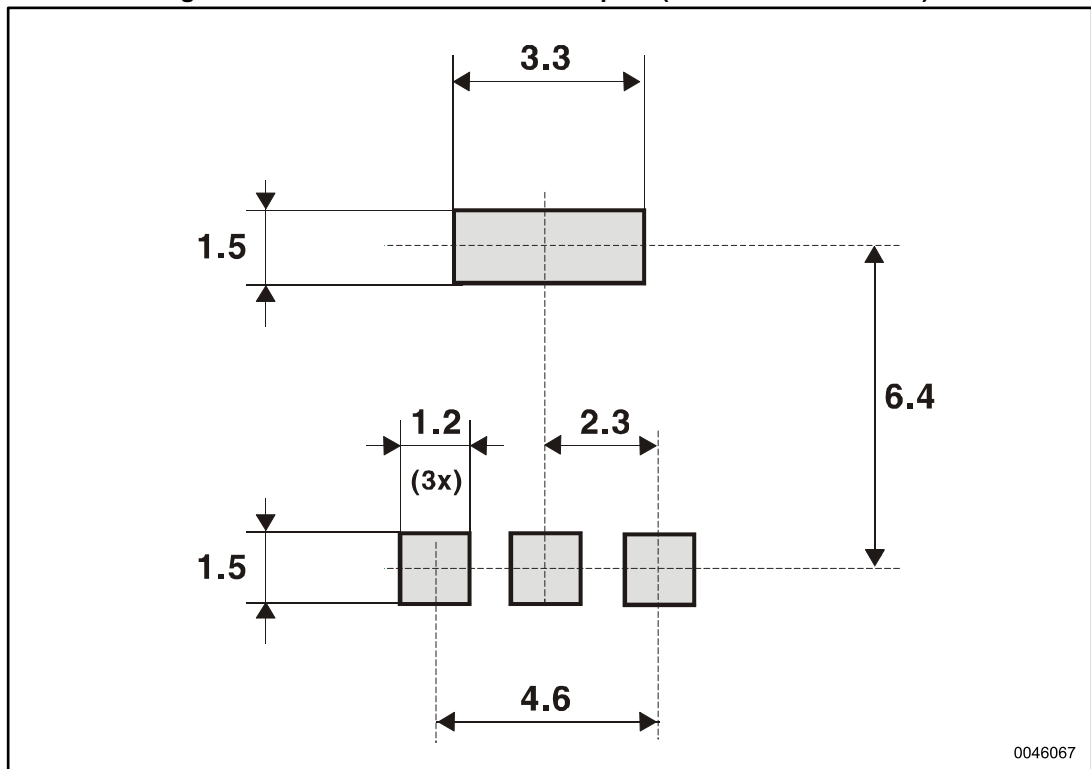


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Table 8: SOT-223 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			1.8
A1	0.02		0.1
B	0.6	0.7	0.85
B1	2.9	3	3.15
c	0.24	0.26	0.35
D	6.3	6.5	6.7
e		2.3	
e1		4.6	
E	3.3	3.5	3.7
H	6.7	7.0	7.3
V			10°

Figure 17: SOT-223 recommended footprint (dimensions are in mm)



## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
02-Aug-2017	1	First release.
07-Feb-2018	2	Updated <i>Section 1: "Electrical ratings"</i> . Added <i>Section 2.1: "Electrical characteristics (curves)"</i> . Minor text changes

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